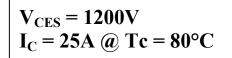
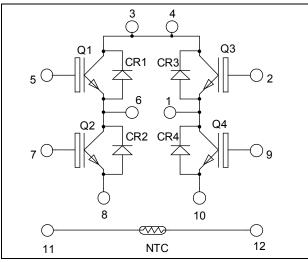
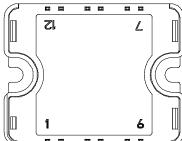
## Full - Bridge High speed Trench + Field Stop IGBT4 Power Module







Pins 3/4 must be shorted together

#### **Application**

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

#### **Features**

- High speed Trench + Field Stop IGBT 4 Technology
  - Low voltage drop
  - Low leakage current
  - Low switching losses
- Very low stray inductance
- Internal thermistor for temperature monitoring

#### **Benefits**

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

### All ratings @ $T_i = 25^{\circ}C$ unless otherwise specified

### Absolute maximum ratings (per IGBT)

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Voltage		1200	V
Ţ	Continuous Collector Current	= 25°C	1200 50 25 100 ±20	
$I_{C}$	Continuous Conector Current $T_C = 80^{\circ}C$	= 80°C	25	Α
$I_{CM}$	Pulsed Collector Current $T_C =$	= 25°C	100	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{D}$	Power Dissipation		165	W

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.



Electrical Characteri	istics (per IGBT)	
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Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				50	μΑ
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$	1.78	2.05	2.42	V
$V_{CE(sat)}$	Conector Emitter Saturation Voltage	$I_C = 25A$	$T_j = 150$ °C		2.6		V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 0.85 \text{ mA}$		5.3	5.8	6.3	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE}$	=0V			150	nA

### **Dynamic Characteristics** (per IGBT)

Symbol	Characteristic	Test Condition	ns	Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			1430		
$C_{oes}$	Output Capacitance	$V_{CE} = 25V$			95		pF
$C_{res}$	Reverse Transfer Capacitance	f = 1MHz			75		
$Q_{G}$	Gate charge	$V_{GE} = 15V, I_C$ $V_{CE} = 960V$	= 25A		115		nC
$T_{d(on)}$	Turn-on Delay Time		Inductive Switching (25°C)		27		
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$			41		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 600V$ $I_{\text{C}} = 25A$			277		
$T_{\mathrm{f}}$	Fall Time	$R_G = 19\Omega$			17		
$T_{d(on)}$	Turn-on Delay Time		Inductive Switching (150°C)		26		
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$			35		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 25A$			347		
$T_{\mathrm{f}}$	Fall Time	$R_G = 19\Omega$			50		
Eon	Turn on Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$	$T_j = 150$ °C		2.4		mJ
$\mathrm{E}_{\mathrm{off}}$	Turn off Energy	$I_C = 25A$ $R_G = 19\Omega$	$T_j = 150$ °C		1.4		1113
$I_{sc}$	Short Circuit data	$V_{GE} \le 15V ; V_1$ $t_p \le 10 \mu s ; T_1 =$			90		A
$R_{thJC}$	Junction to Case Thermal Resistance					0.9	°C/W

### Reverse diode ratings and characteristics (per diode)

Symbol	Characteristic	haracteristic Test Conditions		Min	Typ	Max	Unit
$V_{RRM}$	Peak Repetitive Reverse Voltage					1200	V
$I_{RM}$	Reverse Leakage Current	$V_R = 1200V$				100	μΑ
$I_F$	DC Forward Current		Tc = 80°C		30		A
$V_{\mathrm{F}}$		$I_F = 30A$			2.6	3.1	
	Diode Forward Voltage	$I_F = 60A$			3.2		V
		$I_F = 30A$	$T_{j} = 125^{\circ}C$		1.8		
ŧ	Reverse Recovery Time		$T_j = 25^{\circ}C$		300		ne
t <sub>rr</sub>	Reverse Recovery Time	$I_F = 30A$ $V_R = 800V$ $T_j$	$T_{j} = 125^{\circ}C$		380		ns
Q <sub>rr</sub>	Payara Pagayary Chargo	$di/dt = 200 A/\mu s$	$T_j = 25$ °C		360		пC
	Reverse Recovery Charge		$T_{j} = 125^{\circ}C$		1700		IIC
$R_{thJC}$	Junction to Case Thermal Resistance					1.2	°C/W



#### Thermal and package characteristics

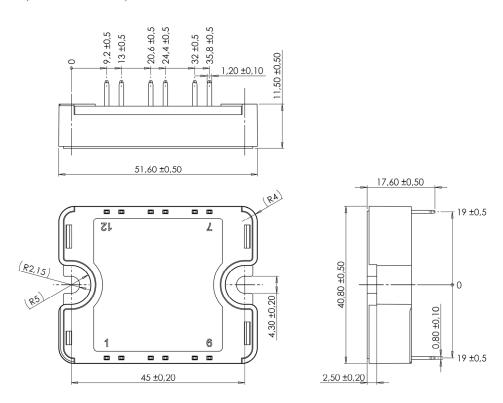
Symbol	Characteristic				Max	Unit
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
$T_{J}$	Operating junction temperature range			-40	175	
$T_{JOP}$	Recommended junction temperature under switching conditions			-40	T <sub>J</sub> max -25	°C
$T_{STG}$	Storage Temperature Range			-40	125	
$T_{\rm C}$	Operating Case Temperature				125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				80	g

### Temperature sensor NTC (see application note APT0406 on www.microsemi.com).

Symbol	Characteristic		Min	Тур	Max	Unit
R <sub>25</sub>	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B <sub>25/85</sub>	$T_{25} = 298.15 \text{ K}$			3952		K
ΔΒ/Β		T <sub>C</sub> =100°C		4		%

$$R_T = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature} \\ R_T: \text{ Thermistor value at T}$$

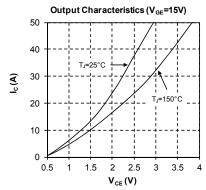
#### Package outline (dimensions in mm)

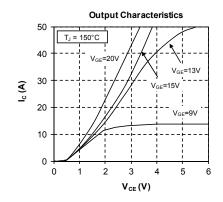


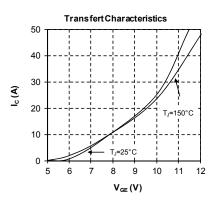
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

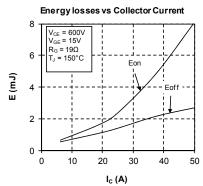


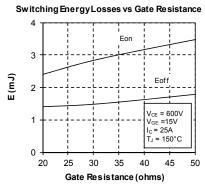
### **Typical Performance Curve**

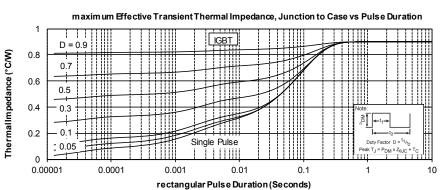






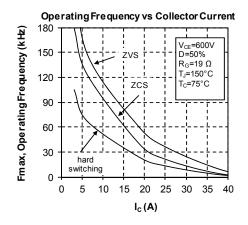


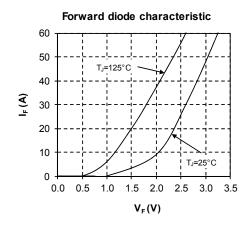




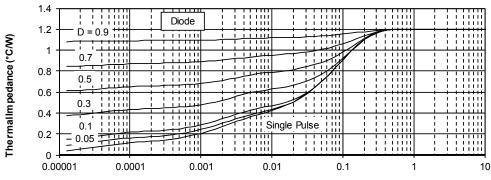


#### Power Matters.™





#### maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration





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